## HI-SEMICON

# SC3D16065I

## 650V Silicon Carbide Schottky Diode

#### **GENERAL DESCRIPTION**

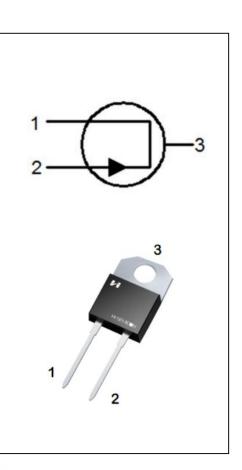
- ♦650V Schottky rectifier
- Zero reverse recovery current/voltage
- High frequency operation
- Switching characteristics independent of temperature
- ◆ Positive temperature coefficient of forward voltage(V<sub>F</sub>)

#### BENEFIT

- ◆ Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- ♦ higher efficiency
- ◆Reduction of heat requirements
- ◆Parallel devices without thermal runaway

#### Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supply (UPS)
- ◆Free wheeling diodes in inverter stages
- ◆LED lighting power
- AC/DC Converters



#### **ORDERING INFORMATION**

Part No.	Package	Marking	Material	Packing
SC3D16065I	TO-220A-2L	C3D16065I	Pb free	Tube

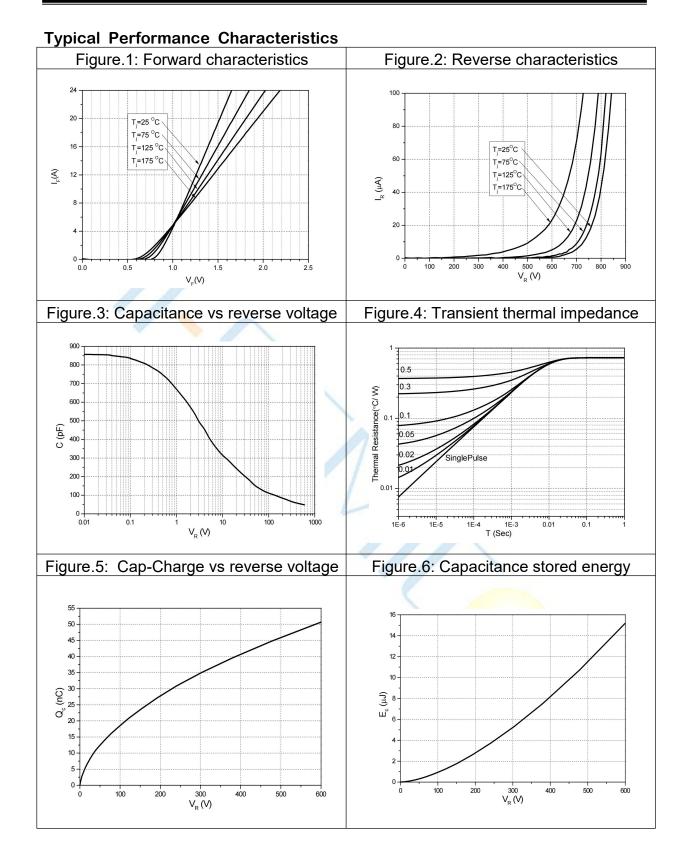
Characteristics	Symbol	Ratings	Unit		
Repetitive peak reverse voltage	V <sub>RRM</sub>	650	V		
Maximum DC blocking voltage	V <sub>DC</sub>	650	V		
Surge peak reverse voltage		Vrsm	650	V	
Continuous forward current	Tc=135℃	IF	16	А	
Repetitive peak forward surge current	tp=10ms Tc=25℃	I <sub>FRM</sub>	103	А	
Non-repetitive peak forward surge curre	I <sub>FSM</sub>	135	А		
	T <sub>C</sub> =25℃		203	w	
Power dissipation	Tc=110℃	P <sub>tot</sub>	91		
Operating junction temperature	Tj	-55~175			
Storage temperature range	T <sub>stg</sub>	-55~175	⊃°C		
Maximum lead temperature for soldering from case for 5 seconds	TL	300	°C		

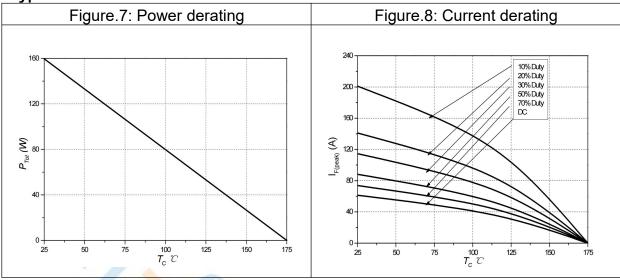
### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Тур.	Max.	Unit	
		I <b>⊧=16A, Tj=25</b> ℃		1.47	1.8	.,	
Forward voltage drop	VF	I <sub>F</sub> =16A, Tj=175℃		1.75	3.0	V	
	I <sub>R</sub>	V <sub>R</sub> =650V, T <sub>j</sub> =25℃		20			
Reverse leakage current		V <sub>R</sub> =650V, Tj=175℃			80	80 uA	
	С	V <sub>R</sub> =0V, f=1MHz		853.3			
Total capacitance		V <sub>R</sub> =200V, f=1MHz		82.7		pF	
		V <sub>R</sub> =400V, f=1MHz	_	61.5			
Total capacitance charge	Qc	V <sub>R</sub> =400V, T <sub>j</sub> =25℃		42.6		nC	
Capacitance stored energy	Ec	V <sub>R</sub> =400V		8.5		uJ	

#### THERMAL CHARACTERISTICS

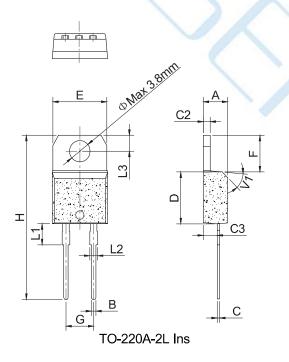
Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	2.7	°C/W





## **Typical Performance Characteristics**

## Package Dimensions of TO-220A-2L



	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	4.40	-	4.60	0.173		0.181	
В	0.61		0.88	0.024		0.035	
C	0.46	1	0.70	0.018		0.028	
C2	1.21	1	1.32	0.048		0.052	
C3	2.40		2.72	0.094		0.107	
D	8.60		9.70	0.339		0.382	
Е	9.80		10.4	0.386		0.409	
F	6.55		<mark>6.9</mark> 5	0.2 <mark>58</mark>		0.274	
G		5.08			0.2		
Н	28.0		29.8	1.102	1	1.173	
L1		3.75	1	-//	0.148		
L2	1.14		1.70	0.045		0.067	
L3	2.65		2.95	0.104		0.116	
V1		45°			45°	-	

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